

# NTST40H120ECTG

## Very Low Leakage Trench-based Schottky Rectifier

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

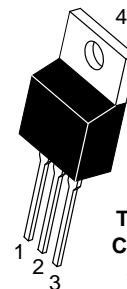
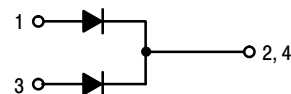


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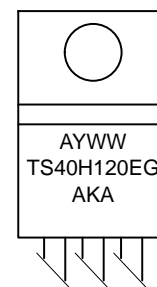
**VERY LOW LEAKAGE,  
SCHOTTKY BARRIER  
RECTIFIERS 40 AMPERES,  
120 VOLTS**

### PIN CONNECTIONS



TO-220AB  
CASE 221A  
STYLE 6

### MARKING DIAGRAM



TO-220AB

A = Assembly Location  
Y = Year  
WW = Work Week  
AKA = Polarity Designator  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# NTST40H120ECTG

## MAXIMUM RATINGS

| Rating  | Symbol                                 | Value       | Unit             |
|---|--|-------------|------------------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage  | $V_{RRM}$<br>$V_{RWM}$<br>$V_R$        | 120         | V                |
| Average Rectified Forward Current<br>(Rated $V_R$ , $T_C = 124^\circ\text{C}$ )<br>(Rated $V_R$ , $T_C = 134^\circ\text{C}$ )   | $I_{F(AV)}$<br>Per device<br>Per diode | 40<br>20    | A                |
| Peak Repetitive Forward Current<br>(Rated $V_R$ , Square Wave, 20 kHz, $T_C = 120^\circ\text{C}$ )<br>(Rated $V_R$ , Square Wave, 20 kHz, $T_C = 130^\circ\text{C}$ ) | $I_{FRM}$<br>Per device<br>Per diode   | 80<br>40    | A                |
| Nonrepetitive Peak Surge Current<br>(Surge applied at rated load conditions halfwave, single phase, 60 Hz)  | $I_{FSM}$                              | 250         | A                |
| Operating Junction Temperature  | $T_J$                                  | -40 to +150 | $^\circ\text{C}$ |
| Storage Temperature   | $T_{stg}$                              | -40 to +150 | $^\circ\text{C}$ |
| Voltage Rate of Change<br>(Rated $V_R$ )  | dV/dt                                  | 36          | V/ns             |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

| Rating   | Symbol                             | NTST40H120ECTG | Unit                                     |
|--|------------------------------------|----------------|--|
| Maximum Thermal Resistance per Device<br>Junction-to-Case<br>Junction-to-Ambient | $R_{\theta JC}$<br>$R_{\theta JA}$ | 0.81<br>70     | $^\circ\text{C/W}$<br>$^\circ\text{C/W}$ |

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

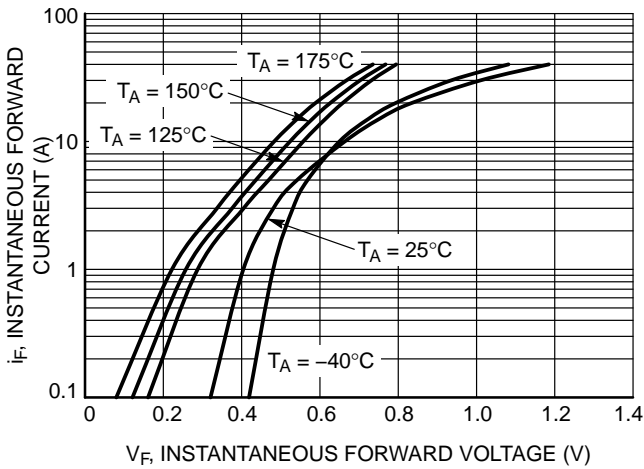
| Rating  | Symbol | Typ  | Max                                 | Unit   |
|---|--------|--|-------------------------------------|--|
| Maximum Instantaneous Forward Voltage (Note 1)<br>( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ )<br>( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ )<br>( $I_F = 20\text{ A}$ , $T_J = 25^\circ\text{C}$ )<br><br>( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ )<br>( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ )<br>( $I_F = 20\text{ A}$ , $T_J = 125^\circ\text{C}$ ) | $V_F$  | 0.54<br>0.67<br>0.84<br><br>0.47<br>0.56<br>0.66 | -<br>-<br>0.93<br><br>-<br>-<br>0.7 | V  |
| Maximum Instantaneous Reverse Current (Note 1)<br>( $V_R = 90\text{ V}$ , $T_J = 25^\circ\text{C}$ )<br>( $V_R = 90\text{ V}$ , $T_J = 125^\circ\text{C}$ )<br><br>(Rated dc Voltage, $T_J = 25^\circ\text{C}$ )<br>(Rated dc Voltage, $T_J = 125^\circ\text{C}$ )  | $I_R$  | 3<br>5<br><br>-<br>7                             | -<br>-<br><br>25<br>28              | $\mu\text{A}$<br>mA<br><br>$\mu\text{A}$<br>mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

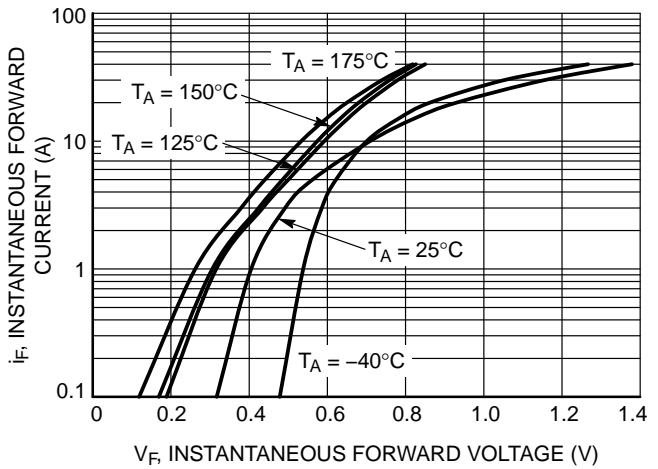
1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

# NTST40H120ECTG

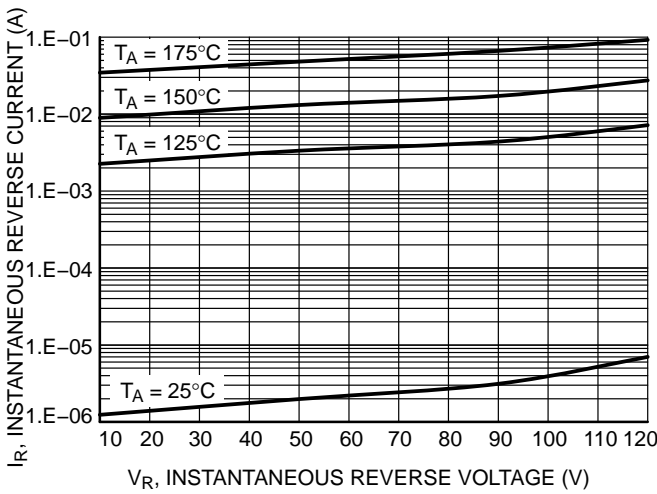
## TYPICAL CHARACTERISTICS



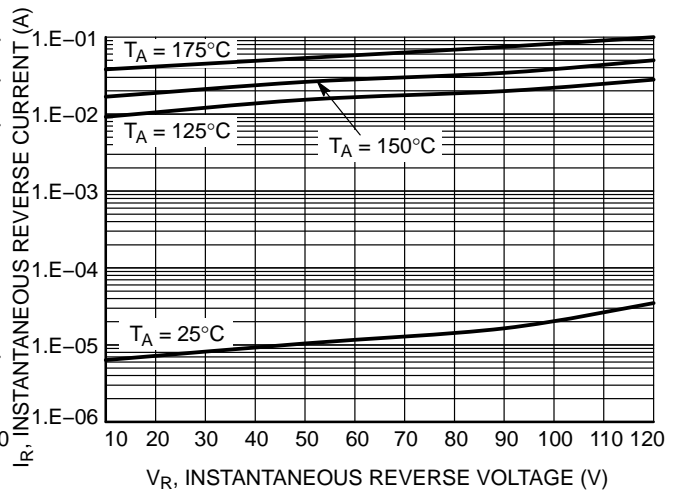
**Figure 1. Typical Instantaneous Forward Characteristics**



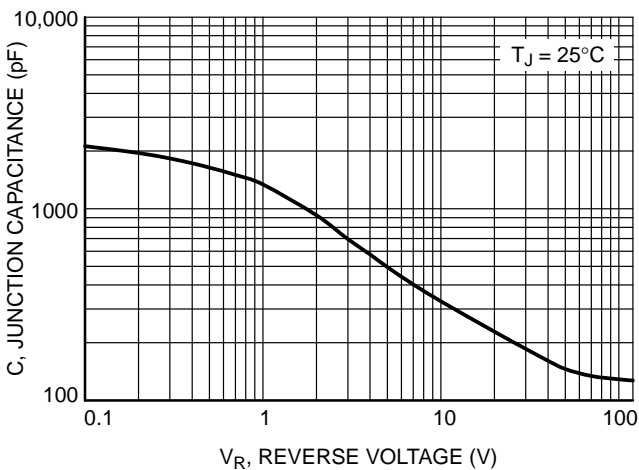
**Figure 2. Maximum Instantaneous Forward Characteristics**



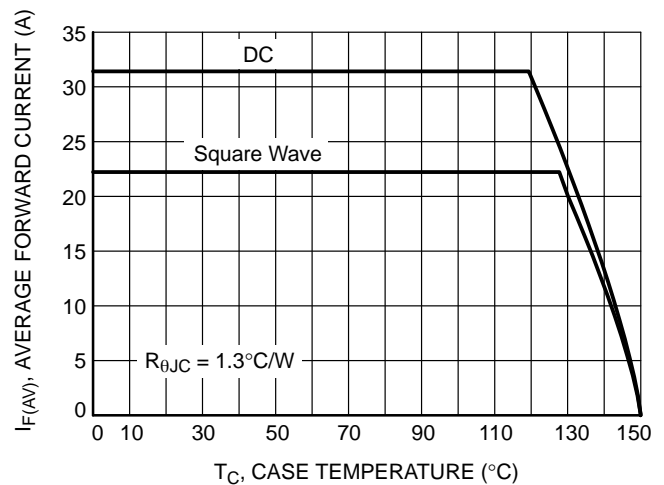
**Figure 3. Typical Reverse Characteristics**



**Figure 4. Maximum Reverse Characteristics**



**Figure 5. Typical Junction Capacitance**



**Figure 6. Current Derating per Diode**

# NTST40H120ECTG

## TYPICAL CHARACTERISTICS

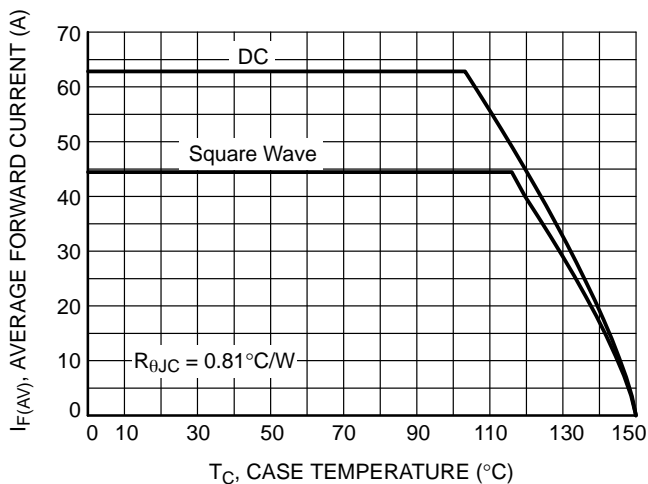


Figure 7. Current Derating per Device

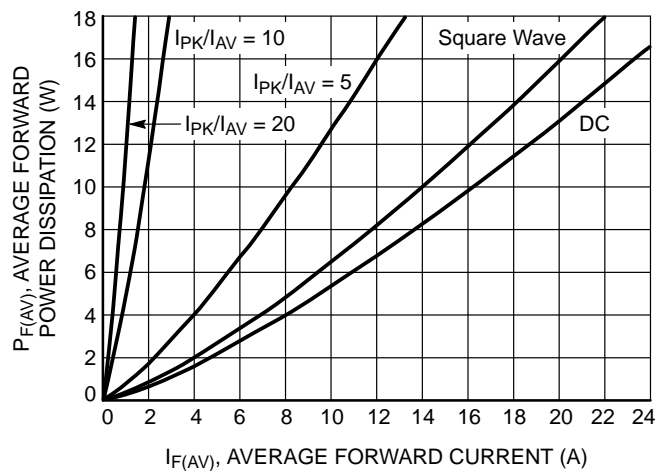


Figure 8. Forward Power Dissipation

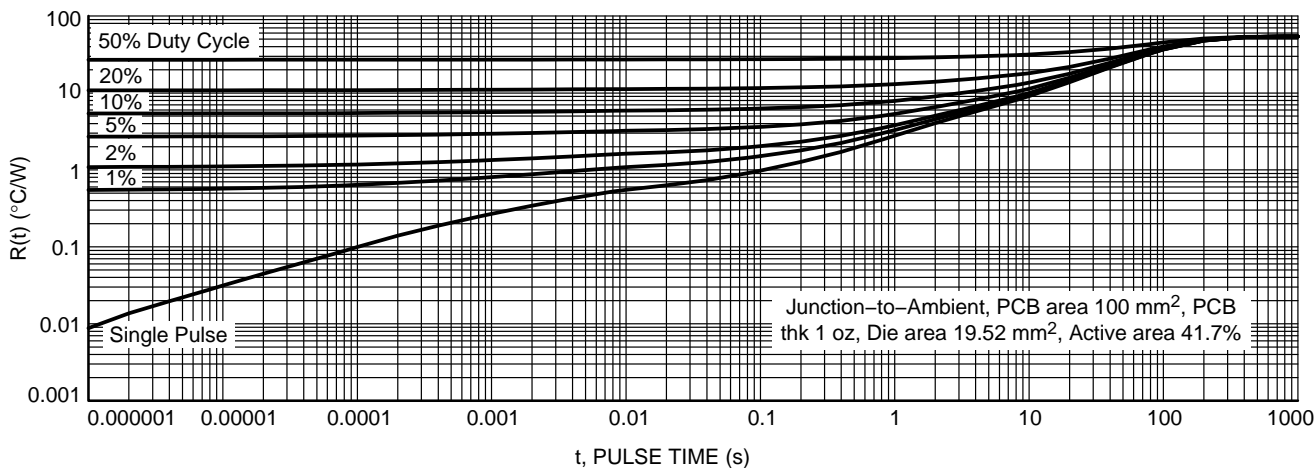


Figure 9. Thermal Characteristics

### ORDERING INFORMATION

| Device         | Package               | Shipping        |
|----------------|-----------------------|-----------------|
| NTST40H120ECTG | TO-220AB<br>(Pb-Free) | 50 Units / Rail |

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1



## TO-220 CASE 221A ISSUE AK

DATE 13 JAN 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.570  | 0.620 | 14.48       | 15.75 |
| B   | 0.380  | 0.415 | 9.66        | 10.53 |
| C   | 0.160  | 0.190 | 4.07        | 4.83  |
| D   | 0.025  | 0.038 | 0.64        | 0.96  |
| F   | 0.142  | 0.161 | 3.60        | 4.09  |
| G   | 0.095  | 0.105 | 2.42        | 2.66  |
| H   | 0.110  | 0.161 | 2.80        | 4.10  |
| J   | 0.014  | 0.024 | 0.36        | 0.61  |
| K   | 0.500  | 0.562 | 12.70       | 14.27 |
| L   | 0.045  | 0.060 | 1.15        | 1.52  |
| N   | 0.190  | 0.210 | 4.83        | 5.33  |
| Q   | 0.100  | 0.120 | 2.54        | 3.04  |
| R   | 0.080  | 0.110 | 2.04        | 2.79  |
| S   | 0.045  | 0.055 | 1.15        | 1.41  |
| T   | 0.235  | 0.255 | 5.97        | 6.47  |
| U   | 0.000  | 0.050 | 0.00        | 1.27  |
| V   | 0.045  | ---   | 1.15        | ---   |
| Z   | ---    | 0.080 | ---         | 2.04  |

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

|                  |             |  |
|------------------|-------------|--|
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